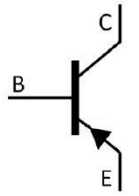
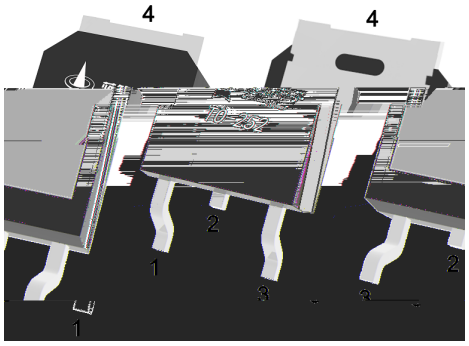
Silicon PNP transistor in a TO-252 Plastic Package.

Excellent hFE linearity, low $V_{CE(sat)}$, high P_C, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

Audio frequency amplifier and switching, especially in hybrid integrated circuits applications, Meet the stringent requirements of automotive applications.





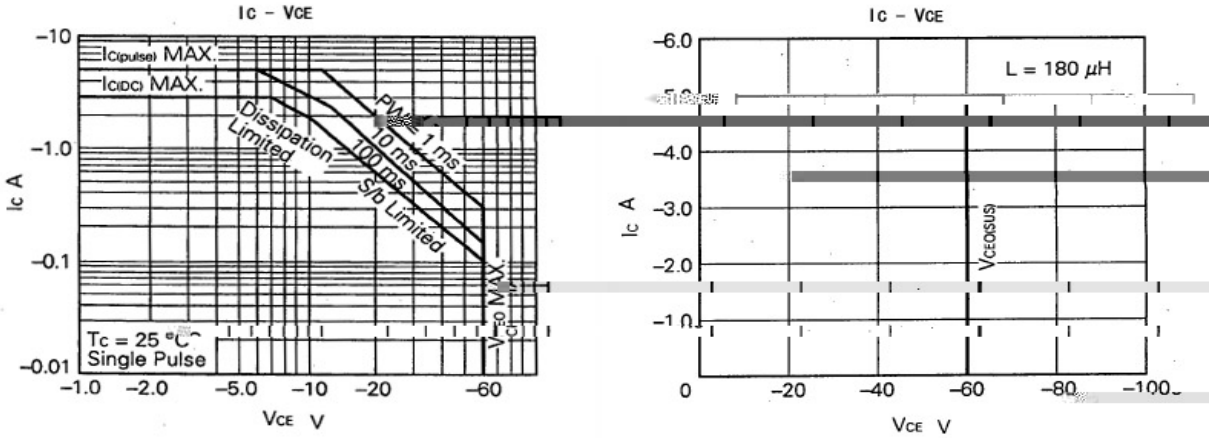
PIN1 Base PIN 2,4 Collector PIN 3 Emitter

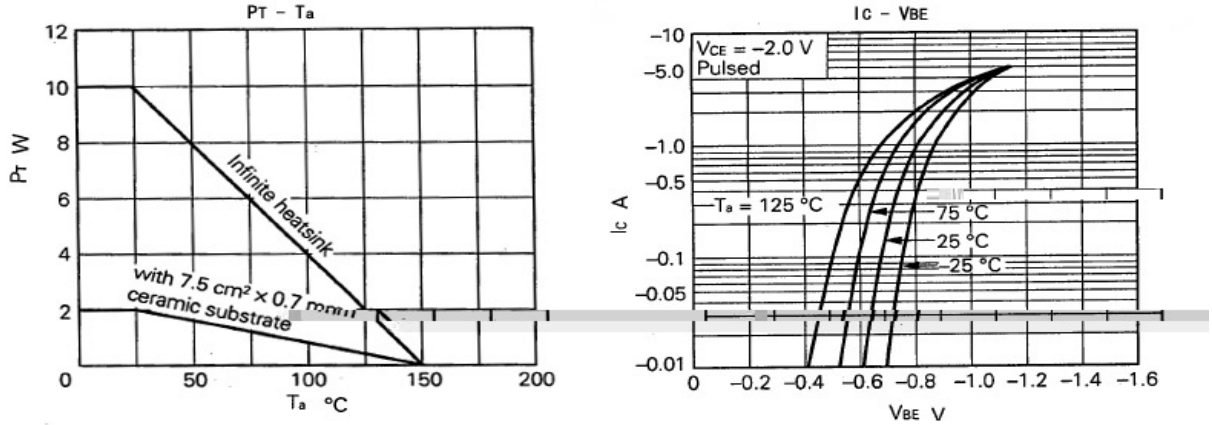
h_{FE} Classifications Symbol	M	L	K
h_{FE} Range	100 200	160 320	200 400

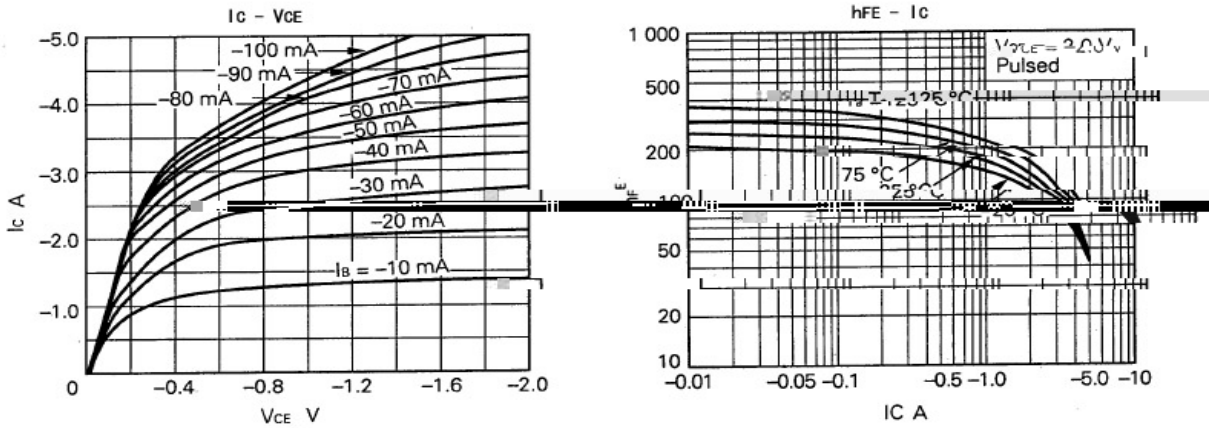
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	I_C	-3.0	A
Collector Power Dissipation*	*P_C	2.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

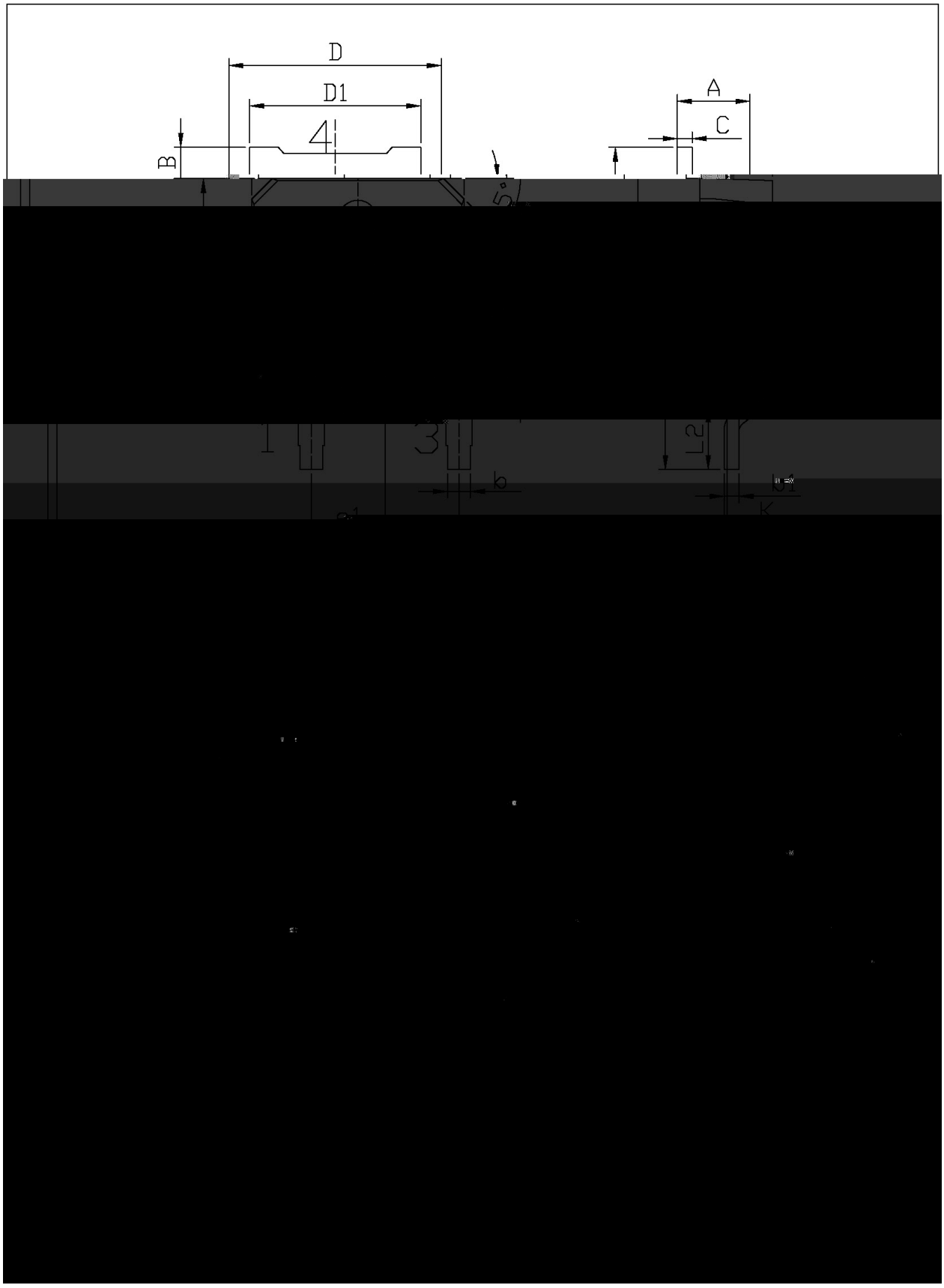
*When mounted on a 7.5×7.5×0.7mm ceramic board.

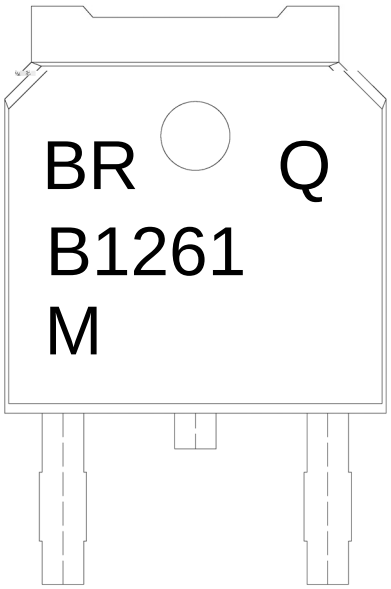
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-60			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-0.1mA I_C=0	-7.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-60V I_E=0			-10	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-7.0V I_C=0			-10	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-2.0V I_C=-600mA	100		400	
	$h_{FE(2)}$	V_{CE}=-2.0V I_C=-200mA	60			
	$h_{FE(3)}$	V_{CE}=-2.0V I_C=-2.0A	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-1.5A I_B=-150mA			-0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-1.5A I_B=-150mA			-1.2	V
Transition Frequency	f_T	V_{CE}=-5.0V I_C=-1.5A		50		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=1.0MHz		40		pF
Turn-On Time	t_{on}	V_{CC}=-10V I_C=-1.0A I_{B1}=-I_{B2}=-0.1A R_L=10Ω			0.5	us
Storage Time	t_{stg}				2.0	
Fall Time	t_f				0.5	


IC – VCE
ICP(pulse) MAX.
IC(DC) MAX.
Dissipation Limited
PW = 1 ms
10 ms
100 ms
S/b Limited
VCEO MAX.
TC = 25 °C
Single Pulse
IC A
VCE V
IC – VCE
L = 180 μH
VCEO(SUS)
IC A
VCE V


PT – Ta
Infinite heatsink
with 7.5 cm² × 0.7 mm
ceramic substrate
PT W
Ta °C
IC – VBE
VCE = –2.0 V
Pulsed
Ta = 125 °C
75 °C
25 °C
–25 °C
IC A
VBE V


IC – VCE
–100 mA
–90 mA
–80 mA
–70 mA
–60 mA
–50 mA
–40 mA
–30 mA
–20 mA
IB = –10 mA
IC A
VCE V
hFE – IC
Pulsed
75 °C
25 °C
hFE
IC A


D
D1
4
B
A
C
5°
1
3
2
b
b1
K



BR

Q

h_{FE}

Note:

BR:	Company Code
Q:	Automobile halogen-free product Code
B1261:	Product Type
M:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No

Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

1	150 200 60 120sec;	1.Preheating:150~200 , Time:60~120sec.
2	255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type	Units					Dimension mm (unit mm³)		